

*Electronic Supplementary Information*

**Piezoresistance in Si<sub>3</sub>N<sub>4</sub> Nanobelts: Toward Highly Sensitive and Reliable  
Pressure Sensors**

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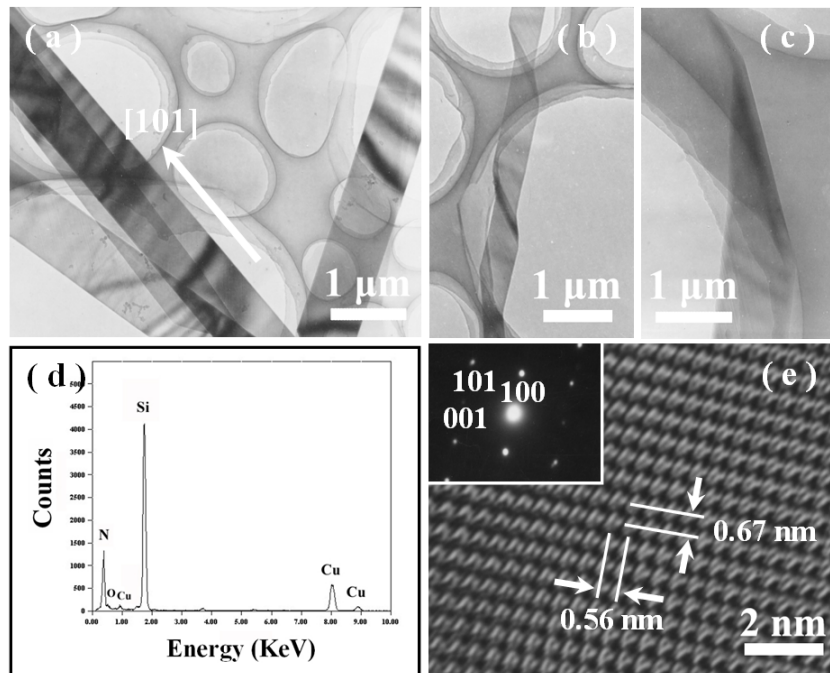
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**TEM Characterization of the  $\text{Si}_3\text{N}_4$  Nanobelts:**



**Fig. S1** (a) A typical TEM image of the flat  $\text{Si}_3\text{N}_4$  nanobelts. (b) and (c) two typical TEM image showing the flat and curved  $\text{Si}_3\text{N}_4$  nanobelts, respectively. (d) A representative EDS spectrum obtained from an individual nanobelt recorded under TEM. (e) HRTEM image of the  $\text{Si}_3\text{N}_4$  nanobelt with the corresponding SAED pattern recorded from a single nanobelt.

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